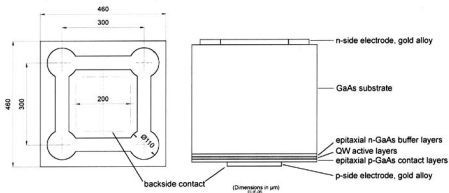


Preliminary

Radiation	Type	Technology	Electrodes
Infrared	ELC-1020-28	InGaAs/GaAs QW structure	P (anode) down N (cathode) up

Outline (dimensions in microns)



Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.1	1.3	V
Reverse voltage	$I_R = 100 \mu\text{A}$	V_R	5			V
Radiant power	$I_F = 20 \text{ mA}$	Φ_e	0.5	0.7		mW
Radiant power	$I_F = 100 \text{ mA}$	Φ_e		1.5		mW
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p		1020		nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		80		nm

Labeling

Type	Lot N°	Φ_e (typ, min, max)	Quantity
ELC-1020-28			

Packing

Chips on adhesive film with wire-bond side on top